

PROCEEDINGS OF SPIE

# ***Nanoepitaxy: Materials and Devices III***

**Nobuhiko P. Kobayashi**  
**A. Alec Talin**  
**M. Saif Islam**  
*Editors*

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# Contents

v *Conference Committee*

---

## SESSION 1 NANOWIRES I

---

- 8106 03 **Nanowire based heterostructures: fundamental properties and applications (Invited Paper)** [8106-03]  
M. Heiss, C. Colombo, A. Fontcuberta i Morral, Ecole Polytechnique Fédérale de Lausanne (Switzerland)

---

## SESSION 2 NANOEPITAXIAL SYNTHESIS I

---

- 8106 08 **Copper oxide thin-film and nanowire for e-textile applications (Invited Paper)** [8106-08]  
J.-W. Han, NASA Ames Research Ctr. (United States); A. Lohn, N. P. Kobayashi, Univ. of California, Santa Cruz (United States); M. Meyyappan, NASA Ames Research Ctr. (United States)

---

## SESSION 3 NANOEPITAXIAL MATERIALS: DEVICE APPLICATIONS I

---

- 8106 0C **Integrated amplifying nanowire FET for surface and bulk sensing (Invited Paper)** [8106-13]  
C. O. Chui, K.-S. Shin, Univ. of California, Los Angeles (United States)

---

## SESSION 4 NANOEPITAXIAL MATERIALS: DEVICE APPLICATIONS II

---

- 8106 0G **Metal oxide nanowire growth for nanotechnology-enhanced device applications (Invited Paper)** [8106-17]  
M. M. Oye, J. Gacusan, O. Lenz, T. Ngo-Duc, J. M. Velazquez, E. Arreola, H. Jethani, M. Rohovie, B. Gigante, A. Kar, B. Kim, A. Hannon, A. Savvinov, Y. Lu, J. Li, M. Meyyappan, Univ. of California, Santa Cruz (United States) and NASA Ames Research Ctr. (United States)
- 8106 0H **Synthesis of crystalline ZnO nanostructures on arbitrary substrates at ambient conditions (Invited Paper)** [8106-18]  
P. K. Vabbina, P. Nayyar, Florida International Univ. (United States); A. P. Nayak, A. M. Katzenmeyer, L. VJ, Univ. of California, Davis (United States); N. Pala, Florida International Univ. (United States); M. S. Islam, Univ. of California, Davis (United States); A. A. Talin, Sandia National Labs. (United States)

---

**SESSION 5 NOVEL CHARACTERIZATION FOR NANOEPITAXIAL MATERIALS**

---

- 8106 0I **Transport in fused InP nanowire device in dark and under illumination: Coulomb staircase scenario (Invited Paper)** [8106-19]  
T. Yamada, Santa Clara Univ. (United States) and Univ. of California, Santa Cruz (United States); H. Yamada, Univ. of California, San Diego (United States); A. J. Lohn, N. P. Kobayashi, Univ. of California, Santa Cruz (United States) and NASA Ames Research Ctr. (United States)
- 8106 0K **Scanning photocurrent microscopy in single nanowire devices (Invited Paper)** [8106-22]  
R. Graham, C. Miller, M. Triplett, D. Yu, Univ. of California, Davis (United States)
- 8106 0L **Growth of ZnO nanowires on retroreflector microspheres and the resulting light channeling and plasmonic properties (Invited Paper)** [8106-23]  
S. M. Prokes, O. J. Glembocki, E. Cleveland, H. Qi, U.S. Naval Research Lab. (United States)

---

**SESSION 6 NANOEPITAXIAL SYNTHESIS II**

---

- 8106 0N **Growth of ZnO-based nanorod heterostructures and their photonic device applications (Invited Paper)** [8106-25]  
J. Yoo, S. T. Picraux, Los Alamos National Lab. (United States); G.-C. Yi, Seoul National Univ. (Korea, Republic of)
- 8106 0P **Compositional grading of In<sub>x</sub>Ga<sub>1-x</sub>As/GaAs tunnel junctions enhanced by ErAs nanoparticles** [8106-27]  
R. Salas, E. M. Krivoy, A. M. Crook, H. P. Nair, S. R. Bank, The Univ. of Texas at Austin (United States)

---

**SESSION 7 NANOEPITAXIAL SYNTHESIS III**

---

- 8106 0Q **Nanocomposites for thermoelectric power generation: rare-earth metal monoantimonide nanostructures embedded in InGaSb and InSbAs ternary alloys** [8106-28]  
K. J. Norris, Univ. of California, Santa Cruz (United States) and NASA Ames Research Ctr. (United States); T. Onishi, Univ. of California, Santa Cruz (United States); A. J. Lohn, N. Padgaonkar, V. Wong, Univ. of California, Santa Cruz (United States) and NASA Ames Research Ctr. (United States); E. Coleman, G. S. Tompa, Structured Materials Industries Inc. (United States); N. P. Kobayashi, Univ. of California, Santa Cruz (United States) and NASA Ames Research Ctr. (United States)
- 8106 0R **Growth of semimetallic ErAs films epitaxially embedded in GaAs** [8106-29]  
A. M. Crook, H. P. Nair, J. H. Lee, D. A. Ferrer, D. Akinwande, S. R. Bank, The Univ. of Texas at Austin (United States)

---

**SESSION 8 NANOWIRES II**

---

- 8106 0X **Indium phosphide nanowires integrated directly on carbon fibers** [8106-35]  
A. J. Lohn, Univ. of California, Santa Cruz (United States) and NASA Ames Research Ctr. (United States); T. J. Longson, Univ. of California, Santa Cruz (United States); N. P. Kobayashi, Univ. of California, Santa Cruz (United States) and NASA Ames Research Ctr. (United States)

*Author Index*

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- 1 Nanowires I  
**Nobuhiko P. Kobayashi**, University of California, Santa Cruz  
(United States)
- 2 Nanoepitaxial Synthesis I  
**A. Alec Talin**, National Institute of Standards and Technology  
(United States)
- 3 Nanoepitaxial Materials: Device Applications I  
**Francois Leonard**, Sandia National Laboratories, California  
(United States)
- 4 Nanoepitaxial Materials: Device Applications II  
**Joan M. Redwing**, The Pennsylvania State University (United States)
- 5 Novel Characterization for Nanoepitaxial Materials  
**M. Saif Islam**, University of California, Davis (United States)  
**Priyalal S. Wijewarnasuriya**, U.S. Army Research Laboratory  
(United States)
- 6 Nanoepitaxial Synthesis II  
**Daniel E. Perea**, Los Alamos National Laboratory (United States)
- 7 Nanoepitaxial Synthesis III  
**Sharka M. Prokes**, U.S. Naval Research Laboratory (United States)
- 8 Nanowires II  
**Nobuhiko P. Kobayashi**, University of California, Santa Cruz  
(United States)